1/f noise in pentacene and poly-thienylene vinylene thin film transistors

Citation for published version (APA):

DOI:
10.1063/1.1423389

Document status and date:
Published: 01/01/2002

Document Version:
Publisher’s PDF, also known as Version of Record (includes final page, issue and volume numbers)

Please check the document version of this publication:

• A submitted manuscript is the version of the article upon submission and before peer-review. There can be important differences between the submitted version and the official published version of record. People interested in the research are advised to contact the author for the final version of the publication, or visit the DOI to the publisher’s website.
• The final author version and the galley proof are versions of the publication after peer review.
• The final published version features the final layout of the paper including the volume, issue and page numbers.

Link to publication

General rights
Copyright and moral rights for the publications made accessible in the public portal are retained by the authors and/or other copyright owners and it is a condition of accessing publications that users recognise and abide by the legal requirements associated with these rights.

• Users may download and print one copy of any publication from the public portal for the purpose of private study or research.
• You may not further distribute the material or use it for any profit-making activity or commercial gain
• You may freely distribute the URL identifying the publication in the public portal.

If the publication is distributed under the terms of Article 25fa of the Dutch Copyright Act, indicated by the “Taverne” license above, please follow below link for the End User Agreement:
www.tue.nl/taverne

Take down policy
If you believe that this document breaches copyright please contact us at:
openaccess@tue.nl
providing details and we will investigate your claim.
1/f noise in pentacene and poly-thienylene vinylene thin film transistors

L. K. J. Vandamme, R. Feyaerts, and Gy Trefán
Department of Electrical Engineering EH 5.15, Eindhoven University of Technology, 5600 MB Eindhoven, The Netherlands

C. Detcheverry
Philips Research Laboratories, 5656 AA Eindhoven, The Netherlands

(Received 25 June 2001; accepted for publication 5 October 2001)

We investigate low frequency conductivity noise in the drain-source channel of organic material field-effect transistors by measuring the spectra of current fluctuations for several values of the gate voltage $V_{gs}$ and drain voltage $V_{ds}$ and find that it is 1/f. The samples are biased in the ohmic range of the applied $V_{ds}$. The relative current 1/f noise is inversely proportional to the charge carrier numbers $N$ generated by illumination or by varying the gate-source voltage. Hooge’s empirical relation for the 1/f noise is validated for these organic semiconductors with an $\alpha=0.01$ for poly-thienylene vinylene and about 100 for pentacene thin film transistors. From geometry dependence of the noise we conclude that series resistance can be ignored for poly-thienylene vinylene field-effect transistors. However, some pentacene samples suffer from a noisy series resistance to the channel resistance. From the 1/f dependence on geometry and gate voltage bias we conclude that it can be used as a diagnostic tool for device quality assessment. © 2002 American Institute of Physics. [DOI: 10.1063/1.1423389]

I. INTRODUCTION

Electrical characteristics$^{1-3}$ and noise$^{4-6}$ in organic materials has been studied to improve the knowledge of the electrical properties. Here we test again if the empirical relation for the 1/f noise used for metal and semiconductors$^7$ is also applicable for organic materials as was shown already in Refs. 4–6. Our aim is to test if 1/f can be used as a diagnostic tool for device quality assessment. In most conductive materials submitted to homogeneous fields one observes a 1/f noise if the number of free carriers is less than $10^{14}$. According to Hooge’s empirical relation under constant voltage conditions, the current fluctuations $S_I/I^2$ are for homogeneous samples submitted to homogeneous fields

$$\frac{S_I}{I^2} = \frac{\alpha}{Nf}$$

with the number of free charge carriers given by $N=l^2/q\mu R$ where $R$ is the sample resistance, $l$ the length of the resistor and $\mu$ the mobility of free charge carriers and $q$ the elementary charge.

To achieve these objectives we do noise measurements by varying channel lengths, the biasing and illumination, to check whether the relative noise is inversely proportional to the number of free carriers $N$. Here we discuss the noise properties of poly-thienylene vinylene (PTV) and pentacene samples produced by Philips Research Laboratories.$^{1-3}$ The low frequency noise analysis turns out to be a superior diagnostic tool for quality problems with some devices.

II. SAMPLES AND MEASUREMENT SETUP

Samples are designed as field-effect transistors (FET) and constructed in a bottom drain and source contact thin film transistor layout.$^3$ The polysilicon on top of a glass substrate forms the gate electrode (first layer), topped with an about 0.25-μm-thick oxide layer that forms the gate oxide (second layer). Gold source and drain electrodes are defined with conventional lithography (third layer). The top layer (channel) is made from a spin coated organic material that is PTV or pentacene. The FETs have p-type channels, with widths $W=500$ or 1000 μm and lengths $L=1.25, 2.5, 5, 10, 20$, and $40$ μm, respectively. The FETs operate in accumulation. To contact the drain and source we scratch through the polymer layer. To measure the noise we use a shielded probe station. Due to the low conductivity of polymers the sample resistances $R_s$ are in the GΩ range. Noise due to conductance fluctuations in sample impedances higher than input resistance $R_{IV}$ of a low noise voltage amplifier can be better observed with a low-noise current (transconductance) amplifier (Brookdeal 5002) in series with the impedance. Then the current fluctuations $S_I$ are measured under a constant voltage bias as is shown in Fig. 1 with $R_V$ short circuited. With a current amplifier the corner frequency between the thermal noise and the 1/f noise of the sample is higher and conductance fluctuations can be investigated better over a larger bandwidth.$^8$ The conductance between source and drain is changed either by applying a gate voltage or illumination. The pentacene samples were illuminated from a distance of about 50 cm using a 12 V dc, 100 W halogen lamp of which we vary the current in steps of 2 A.

$^4$Electronic mail: L.K.J.Vandamme@tue.nl
III. RESULTS

A. PTV

PTV samples have a spaghetti-like microstructure. They are easily damaged by high fields \( E > 18 \text{ kV/cm} \) and electrostatic discharge. Their drain and source resistances in dark are between \( 5 \text{ M}\Omega \) and \( 10 \text{ G}\Omega \) for gate voltages of about \(-9 \) to \(-22 \text{ V} \). Settling times after changing the bias conditions are rather short, and therefore the drift during the measurements is relatively small. This is important in order to suppress the \( 1/f^2 \) drift contributions in the spectrum at low frequencies.

We measured the spectra of current fluctuations at a fixed gate-source voltage while changing drain voltages \((V_{ds} = 1.5, 3.0, 4.5 \text{ V})\). We found that they are \( 1/f \) and background noise. The spacing indicates different drain-source current levels.

![FIG. 1. On-wafer level measurement setup. The drain-source current is set by a battery for the drain with voltage \( V_{bat} \) and another battery for the gate with voltage \( V_{gs} \), both can be changed in steps. The current fluctuations in \( I_n \) are amplified by a Brookdeal 5002 low-noise current amplifier whose output is lead in an HP 3566A or Advantest R9211E spectrum analyzer in a bandwidth from 1 Hz up to 100 kHz.](image)

FIG. 1. On-wafer level measurement setup. The drain-source current is set by a battery for the drain with voltage \( V_{bat} \) and another battery for the gate with voltage \( V_{gs} \), both can be changed in steps. The current fluctuations in \( I_n \) are amplified by a Brookdeal 5002 low-noise current amplifier whose output is lead in an HP 3566A or Advantest R9211E spectrum analyzer in a bandwidth from 1 Hz up to 100 kHz.

FIG. 2. Current noise spectra \( S_f \) in a PTV sample for drain-source voltages \( V_{ds} = -1.5, -3, \) and \(-4.5 \text{ V} \), respectively. The spectra show \( 1/f \) and background noise. The spacing indicates different drain-source current levels.

We investigated for a given geometry \( S_f/I^2 \) vs \( V_{gs} \) and found \( S_f/I^2 \propto 1/V_{gs} \) in agreement with Eq. (1). We measured the dependence of the relative noise on the gate voltage \( V_{gs} \). We found that \( S_f/I^2 \propto 1/V_{gs} \) as is expected and shown in Fig. 3. We also investigated how the noise depends on the geometry since the samples have different lengths \( L = 5, 10, 20, 40 \mu \text{m} \) (FETs with channel length of \( L \leq 2.5 \mu \text{m} \) often were detected to be short circuits). We measured the low frequency current noise \( S_f \) at \( V_{gs} = -9 \) to \(-22 \text{ V} \) and \( V_{ds} = -1.5 \) to \(-4.5 \text{ V} \). We found \( S_f/I^2 \propto 1/L \) which is in agreement with the empirical relation for ohmic samples (see Fig. 4). Calculated \( \alpha \) values using Eq. (1) are in the range of 0.01-0.08 using mobilities \( \mu = 10^{-3} - 10^{-4} \text{ cm}^2/\text{V s} \). These are observed mobilities calculated from a relation \( \mu = L^2 g_m/(WC_{ds}) \) where \( g_m = dI/dV_{gs} \) the transconductance and \( C_{ds} \) the oxide capacitance per unit area.

![FIG. 3. The relative noise \( S_f/I^2 \) taken at \( f = 1 \text{ Hz} \) dependence on the gate voltage \( V_{gs} \). The inverse proportionality with \( V_{gs} \) is expected, because the relative noise in Ohmic samples is inversely proportional to the number of free carriers \((N \times V_{gs})\) and \( S_f/I^2 = a/V_{gs} \) at least if \( a \) is \( V_{gs} \) independent.](image)

FIG. 3. The relative noise \( S_f/I^2 \) taken at \( f = 1 \text{ Hz} \) dependence on the gate voltage \( V_{gs} \). The inverse proportionality with \( V_{gs} \) is expected, because the relative noise in Ohmic samples is inversely proportional to the number of free carriers \((N \times V_{gs})\) and \( S_f/I^2 = a/V_{gs} \) at least if \( a \) is \( V_{gs} \) independent.

![FIG. 4. Geometry dependence of the relative current \( 1/f \) noise on a PTV sample. \( S_f/I^2 \) (taken at 1 Hz with \( V_{ds} = -3 \text{ V} \) and \( V_{gs} = -15.9 \text{ V} \)) is inversely proportional with channel length \( L \) because \( S_f/I^2 \propto 1/L \) for samples biased at the same \( V_{gs} \) and having the same width. This fact indicates an ohmic sample without serious contact noise contributions and proves the validity of the empirical relation of Eq. (1).](image)

FIG. 4. Geometry dependence of the relative current \( 1/f \) noise on a PTV sample. \( S_f/I^2 \) (taken at 1 Hz with \( V_{ds} = -3 \text{ V} \) and \( V_{gs} = -15.9 \text{ V} \)) is inversely proportional with channel length \( L \) because \( S_f/I^2 \propto 1/L \) for samples biased at the same \( V_{gs} \) and having the same width. This fact indicates an ohmic sample without serious contact noise contributions and proves the validity of the empirical relation of Eq. (1).
resistance measurements we found that measured at 1 Hz noise we find 15 and the oxide capacitance. Our mobility values 10 were calculated for PTV from measuring transconductance ~

leads to radical fields between the electrodes. The inner have concentric circular source and drain electrodes which to analyze the measurement data carefully. 14 Our samples was found already in semiconductors under illumination. 9–1 1 which is in support of the empirical relation. 9–1 1 Through 1/f noise was also observed in silicon, GaAs and GaAlAs which is in support of the empirical relation.6–11 Through resistance measurements we found that measured at 1 Hz S~/I~/2/Rds (see Fig. 5). This result shows the validity of the empirical relation for the current 1/f noise in pentacene as was found already in semiconductors under illumination.6–11 The calculated 2 values from Eq. (1) were of about 1–100 using mobilities μ = 10⁻⁵–10⁻⁴ cm²/V s. The mobilities were calculated for PTV from measuring transconductance and the oxide capacitance. Our mobility values 10⁻⁵–10⁻⁴ cm²/V s are typical for granular pentacene12 and 3–4 orders of magnitude lower than mobilities of single crystal pentacene.13

### IV. ON CALCULATING THE RESISTANCE AND α IN RADIAL FIELDS

Doing 1/f noise measurement with the aim of obtaining a reliable 2 value for quality assessment of material one has to analyze the measurement data carefully.14 Our samples have concentric circular source and drain electrodes which leads to radial fields between the electrodes. The inner circle with radius 1 functions as drain, the outer circle with radius 2 functions as source. In our analysis for resistance and noise dependence on geometry the radial field between the concentric electrodes is approached as homogeneous. We will now investigate if this is a correct approximation. The relative noise S~/R~/2 in such a structure is not given by Eq. (1) but N has to be replaced by an Neff and for the relative noise we find15

\[
\frac{S_R}{R^2} \approx \frac{\alpha [1/r_1^2 - 1/r_2^2]}{4 \pi t n [\ln(r_2/r_1)]^2 f}
\]

with \( r \) being the thickness of the layer and \( n \) the free carrier concentration. If the 2 parameter is calculated by overlooking the nonhomogeneity of the field and is calculated from the experimentally observed relative noise at 1 Hz \( f S~/R^2 \) given by Eq. (2) and by multiplying it with \( N = \pi (r_2^2 - r_1^2) t n \), it results in an apparent 2 which is always larger than the real 2 like

\[
\frac{\alpha_{\text{app1}}}{\alpha} = \frac{(r_2 - r_1)(1/r_1^2 - 1/r_2^2)}{4[\ln(r_2/r_1)]^2}
\]

The continuous line of Fig. 6 shows the error in terms of the ratio \( \alpha_{\text{app1}}/\alpha \) as a function \( r_2/r_1 \). If 2 is calculated by overlooking the radial field but thus applying \( N = L^2 q \mu R \) which holds for homogeneous samples submitted to homogeneous fields, then we find an error \( \alpha_{\text{app2}}/\alpha \) which is expressed by

\[
\frac{\alpha_{\text{app2}}}{\alpha} = \frac{(r_2 - r_1)(1/r_1^2 - 1/r_2^2)}{2[\ln(r_2/r_1)]^2}
\]

This error \( \alpha_{\text{app2}}/\alpha \) is shown by the dashed line in Fig. 6. Figure 6 shows that in the range of 1.01 < \( r_2/r_1 < 1.5 \) \( \alpha_{\text{app1}} \approx \alpha_{\text{app2}} \approx \alpha \), within an error of less than 10%.

The resistance in a radial field is given by

\[
R = \frac{\rho}{2 \pi t} \ln(r_2/r_1)
\]

instead of our approximation \( R_{\text{app}} = \rho (r_2 - r_1)/2 \pi t r_1 \). However, all discussions about geometry dependence in terms of \( L = r_2 - r_1 \) are correct because the error \( R_{\text{app}}/R = (r_2/r_1 - 1)/\ln(r_2/r_1) \) is negligible in the range 1.01 < \( r_2/r_1 < 1.5 \). Hence overlooking the complication due to the radial fields in the calculations of resistance and 2 does not result in large errors for our samples.

![Figure 5](image5.png)

**FIG. 5.** Illumination effects on the relative noise on a pentacene sample. The relative noise \( S~/I~/2 \) measured at 1 Hz varies linearly with the channel resistance \( R \) because \( S~/I~/2 = \mu N q \mu R ~L^2 \) where \( \mu \) is mobility, \( q \) elementary charge and \( R \) channel resistance, respectively. The resistance changes are due to the generation of free carriers by illumination.

![Figure 6](image6.png)

**FIG. 6.** Differences between the apparent \( \alpha \) and the real \( \alpha \) due to ignoring radial field effect by treating the sample as if it were submitted to a homogeneous electric field.
V. ON 1/f NOISE AS A DIAGNOSTIC TOOL

Sometimes we face a situation when current–voltage characteristic indicates a normal device but the low frequency noise analysis indicates quality problems with that device. In these cases the low frequency noise analysis turns out to be a superior diagnostic tool. For instance, in a normal device the relative noise $S_I/I^2 \approx 1/L$ and $1/V_{gs}$. If this proportionality does not hold we consider the device noise anomalous. In some of our pentacene samples we observed this proportionality. In high quality samples the relative noise $S_I/I^2 \approx 1/L$ should be observed as in Fig. 4. In some of our pentacene samples we observed that in some pentacene samples the relative noise $S_I/I^2$ grows with the length $L$ (see Fig. 7) for FETs whose channel length $L>5 \, \mu m$. We also observed that in some pentacene samples the relative noise $S_I/I^2$ grows with the gate voltage $V_{gs}$ (see Fig. 8). In both of the above cases the noise is anomalous. Here we offer four possible explanations for the origins of anomalous noise: (i) a parasitic conductance situated parallel with the channel, (ii) a parasitic resistance in series with the channel, (iii) the dependence of carrier mobility on the gate voltage $V_{gs}$ and (iv) the noise generated by an injection-type current–voltage characteristic, respectively. We note here that in investigating the noise as a function of geometry in an $L$ array (a set of devices all having the same width but different length $L$) we assume that the conductance $G$ and noise parameter $\alpha$ are uniform over the set. If this is not the case then the $L$-array analysis is not applicable.

When considering the complications [case (i)] due to a parasitic parallel conductance $G_p$ to the channel conductance $G_{ch}$ with total conductance $G = G_{ch} + G_p$ and noise $S_G = S_{G_{ch}} + S_{G_p}$ we assume that the conductance is normal and dominated by the channel, i.e., $G \approx G_{ch} \approx L^{-1}$ but the emerging noise is dominated by the parasitic conductance, i.e., $S_G \approx S_{G_p}$ that does not depend on the gate voltage $V_{gs}$. Our experiments suggest that the parasitic conductance noise $S_{G_p}$ must be independent of the channel length $L$ for $L<5 \, \mu m$ and inversely proportional to it for $L>5 \, \mu m$ in order to obtain a relative current noise shown in Fig 7. This noise is anomalous since normally it should be $S_{G_{ch}} \approx L^{-3}$. The complication [case (ii)] takes into account a parasitic noisy resistance $R_x$ in series with the channel generating noise $S_{R_x}$. Both $R_x$ and $S_{R_x}$ are considered to be independent of $L$ as in Refs. 17 and 18. For parasitic series resistance problems we have $R = R_{ch} + R_x$ and $S_R = S_{R_{ch}} + S_{R_x}$ with a dominating channel resistance ($R = R_{ch}$) and parasitic resistance ($S_R = S_{R_x}$). Then the anomalous relative noise derives from a length independent parasitic resistance with noise $S_{R_x}$ becomes proportional to $L^{-2}$. Table I summarizes the above mentioned considerations to explain anomalous trends in the relative current noise.

The type of complication [case (iii)] to explain $x$ and $y$ different from $-1$ is the $1/f$ noise parameter $\alpha$ dependence on mobility $\mu$. The mobility is weakly dependent on the gate voltage. If $\alpha \approx \mu^x$ with $x = 2$ and $\mu \approx V_{gs}^{-y}$ we find $S_I/I^2 \approx V_{gs}^{x+y-1}$. Here we took into account how the channel resistance $R$ depends on the gate voltage $V_{gs}$, i.e., $R \approx 1/\mu \approx 1/V_{gs}^{-y}$. Now we consider $x+y = 1$ with $x = 2$ and $y = 1/2$ which means that we use a well established dependence of $\alpha$ on $\mu$ observed in semiconductors and a weak dependence of $\mu$ on $V_{gs}$ as suggested in Refs. 2 and 3. Such a behavior results in a $S_I/I^2 \approx L^{-1}$ that was observed for short channels (see Fig. 7) and $S_I/I^2 \approx V_{gs}^{0}$ which was not observed (see Fig. 8).

The last complication [case (iv)] considered explaining at the same time a nonohmic current–voltage characteristic and a $S_I/I^2 \approx V_{gs}^y$ with $y \neq -1$ is the injection type of behavior on a microscopic scale between two pentacene single crystals grains. For the current–voltage characteristic then

<table>
<thead>
<tr>
<th>Dominant term $S_I/I^2(L)$</th>
<th>Dominant term $S_I/I^2(V_{gs})$</th>
</tr>
</thead>
<tbody>
<tr>
<td>$G \approx G_{ch} \approx L^{-1}$</td>
<td>$S_G = S_{G_{ch}}$</td>
</tr>
<tr>
<td>$G \approx G_{ch} \approx L^{-1}$</td>
<td>$S_G = S_{G_{ch}}$</td>
</tr>
<tr>
<td>$R = R_{ch}$</td>
<td>$S_R = S_{R_{ch}}$</td>
</tr>
</tbody>
</table>

TABLE I. Complications that explain anomalous relative noise dependence $S_I/I^2 \approx L^x$ with $x \neq -1$ and $S_I/I^2 \approx V_{gs}^y$ with $y \neq -1$.
holds a proportionality in the current–voltage characteristic as \( I \propto V^2 \). For the noise then holds the proportionality \( S_I \propto I^2/V \). So the relative noise for a fixed gate voltage then becomes \( S_I/I^2 \propto V^{-1} \propto I^{-1/2} \). Some of our experimental results are in agreement or at variance with the abovementioned trends.

The best candidate to account for the anomalous noise seems to be (ii) when we assume a noisy series resistance in the channel dominating the noise of the channel but not its resistance. This has often been observed in submicron metal-semiconductor transistors, high electron mobility transistors\(^\text{17} \) and metal-oxide-semiconductor (MOS) transistors\(^\text{18,21,22} \).

**VI. ON BIAS AND GEOMETRY DEPENDENCE AS SHOWN IN LITERATURE**

Necliudov et al. found\(^\text{6} \) in bottom contacted samples which have similar contacts to our pentacene samples, there is a nonlinearity of the injection diode type for small values of the \( V_{ds} \). They suspected that it was caused by poor contact edge coverage due to shadowing of the source and drain contacts. This would explain high local fields and the injection-like behavior in the \( I_d/V_{ds} \) curves. From their noise results we can derive a dependency of \( S_I/I^2 \propto V_{ds}^{-1/2} \) and the rather normal dependence \( S_I/I^2 \propto V_{gs}^{-1} \), which is also present in our longest pentacene samples. The \( \alpha \) values that they present for bottom contacted samples are in the range 5–20, which is again in agreement with what we found in pentacene.

The existence of series resistance contributions in organic thin film transistors can be observed as well from the results by Martin et al. in Ref. 4. From their survey we observe that the relative noise is proportional to \( L^{-3} \) in samples with channel lengths of \( L \geq 12 \ \mu m \) which point to a channel without series resistance contributions. This is true since: \( S_I/I^2 \propto N^{-1} \propto (W/L)^{2} \propto 1/(W/L) \propto W/(L^2) \propto L^{-3} \). However, for lower values of the channel length as often occurs this proportionality no longer holds, indicating a limit caused by a series resistance.

**VII. CONCLUSIONS**

The low frequency noise in PTV samples is due to conduction fluctuations and has the typical 1/f spectrum. In the ohmic region under a constant gate voltage \( S_I/I^2 \) remains constant with \( f \) and with an increasing gate voltage the number of free carriers (holes) increases and the relative 1/f noise drops as predicted in the empirical relation \( S_I/I^2 \propto 1/N \propto 1/V_{gs} \). The pentacene samples have a lower concentration of free carriers than PTV samples and they are more sensitive to light. Under constant bias voltage at drain (−4.5 V) and gate (−22 V) the relative noise \( S_I/I^2 \) drops with increasing light illuminations (\( \Phi \)) as by the empirical relation \( S_I/I^2 \propto 1/N \propto R_{ds}(\Phi) \). Our PTV thin film transistors show no contact noise contributions, as it was observed from the noise versus geometry (\( W/L \)) relations. However, pentacene samples suffered from series resistance contact noise, while the resistance between source and drain was still dominated by the channel resistance which was under control of the gate voltage.

From our noise under illumination investigations it becomes clear that the free carrier transport process in PTV and pentacene is quite different. On one hand, PTV has a behavior considering the 1/f noise as in normal MOS transistors except of the much lower mobility. Pentacene FETs, on the other hand, suffer from a low but noisy series resistance. It has been proved again that the 1/f noise van should be used as a diagnostic tool for quality assessment of prototype devices.

**ACKNOWLEDGMENTS**

This research was partially supported by Science for Peace (SpF 973799) from NATO and COBRA. The authors thank Eduard Meijer from Delft University of Technology for providing data and discussions on the organic transistors.


\(^{8}\)L. K. J. Vandamme and G. Trefán, IEE Proc. Circuits (to be published).


\(^{15}\)L. K. J. Vandamme, Appl. Phys. 11, 89 (1976).


